

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	14	gate with ((two dual double twin) near charge near (storage\$1 trap\$4)) with ((side near wall\$1) sidewall\$1)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2006/01/18 07:31
L2	0	((two dual double twin) near charge near (storage\$1 trap\$4)) near ((side near wall\$1) sidewall\$1)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2006/01/18 07:31
L3	132	gate and ((two dual double twin) near charge near (storage\$1 trap\$4)) and ((side near wall\$1) sidewall\$1)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2006/01/18 07:31
L4	8	memory AND substrate AND well\$1 AND (gate ADJ (insulat\$3 oxide dielectric)) AND (gate ADJ electrode) AND ((two dual twin double) NEAR charg\$3 NEAR (storag\$3 trap\$4)) AND (sidewall (side NEAR wall\$1) spacer\$1) AND channel AND ((diffus\$3 dop\$4 implant\$5) NEAR (area\$1 region\$1)) AND current AND (voltage potential) AND (hole\$1 electron\$1).CLM.	US-PGPUB; USPAT	OR	ON	2006/01/18 07:39